Approved	Checked	Designed	DEVELOPMENT SPECIFICATION	
		T-Tabata	P/N : LNJ211R82RA	TEMPORARY

TYPE	Red Light Emitting Diode
APPLICATION	Indicatiors
MATERIAL	InGaAlP
OUTLINE	Attached

ABSOLUTE MAXIMUM RATINGS	P	*1 I_{FP}	I_{FDC}	V_R	Topr	Tstg
	55	60	20	4	-30～+85	-40～+100
	mW	mA	mA	V	℃	℃
CONDITION	Ta＝25±3℃					

Test Specification

Item	Symbol	Condition	Typ	Limit		Unit
				Min	Max	
Forward Voltage	V_F	I_F＝10mA	1.92		2.5	V
Reverse Leakage Current	I_R	V_R＝ 4V			100	μA
Luminous Intensity *2	I_O	I_F＝10mA DC	15	8		mcd
Peak Emission Wavelength	λp	I_F＝10mA DC	645			nm
Spectral Line Half Width	Δλ	I_F＝10mA DC	22			nm

*1. The Condition of I_{FP} is duty 10 % , Pulse width 1 ms

*2. Tolerance of luminous intensity : ±20%.

NOTE

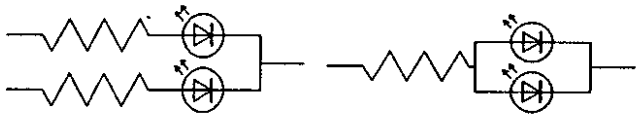
★1. Please contact the Panasonic local office if you design at low current (blow 1mA DC) or pulse current operation and have any questions.

★2. Soldering conditions····Refer to Handling note.

★3. Compositions of the lead ····· Cu/Ni/Au plating

★4. Beware of destruction by static electricity in handling the LED.

★5. Circuit to operate LED.



(A) Recommended circuit.

(B) The difference of brightness between the LED could be found due to the V_F characteristics of each LED.

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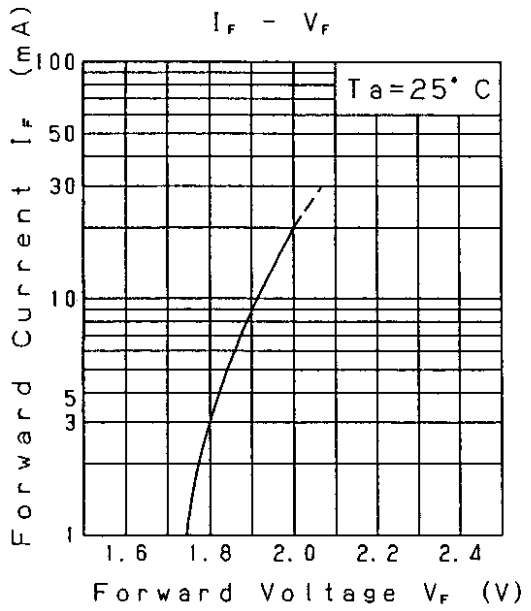

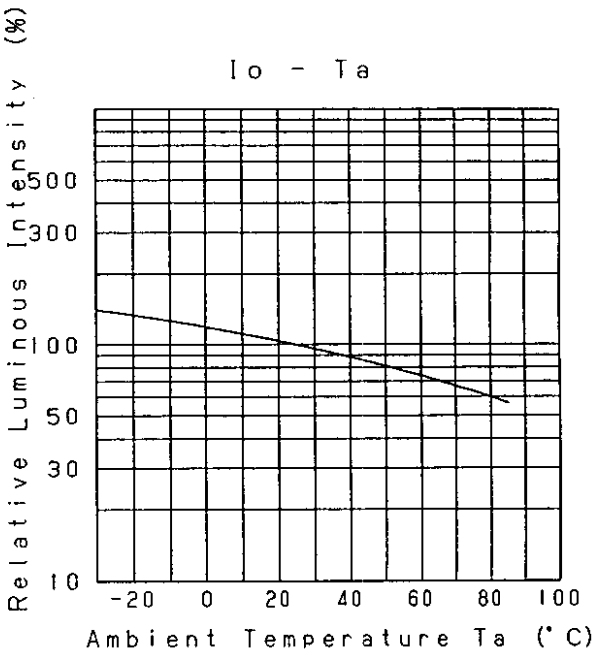

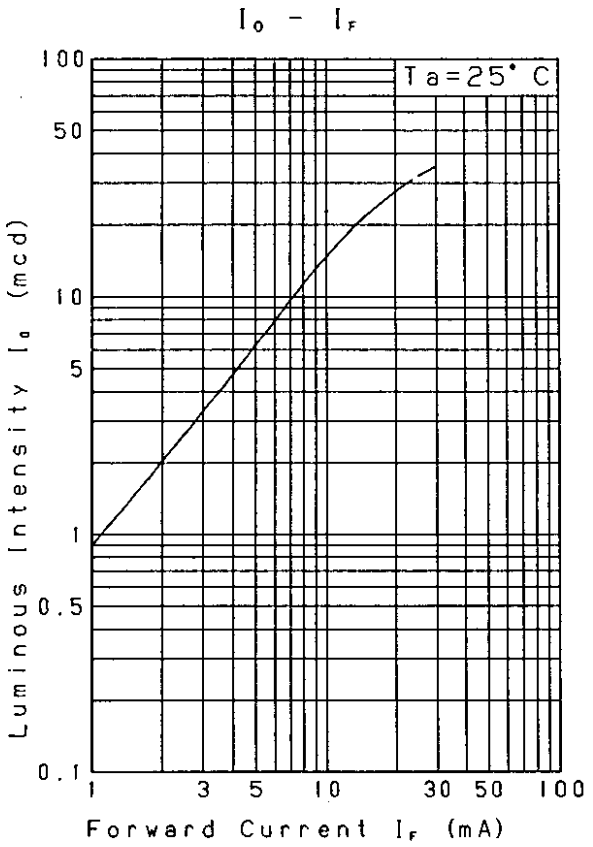

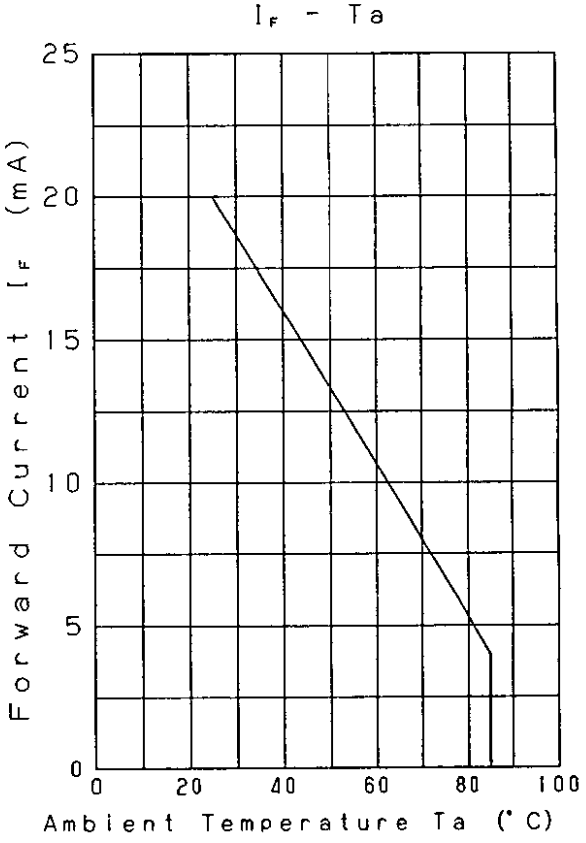

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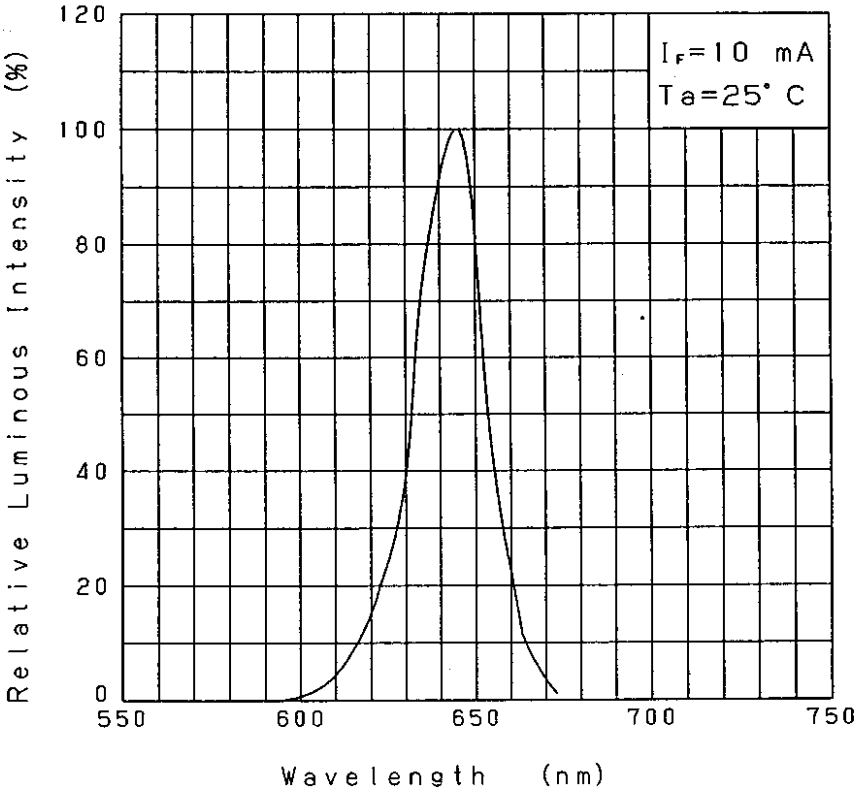
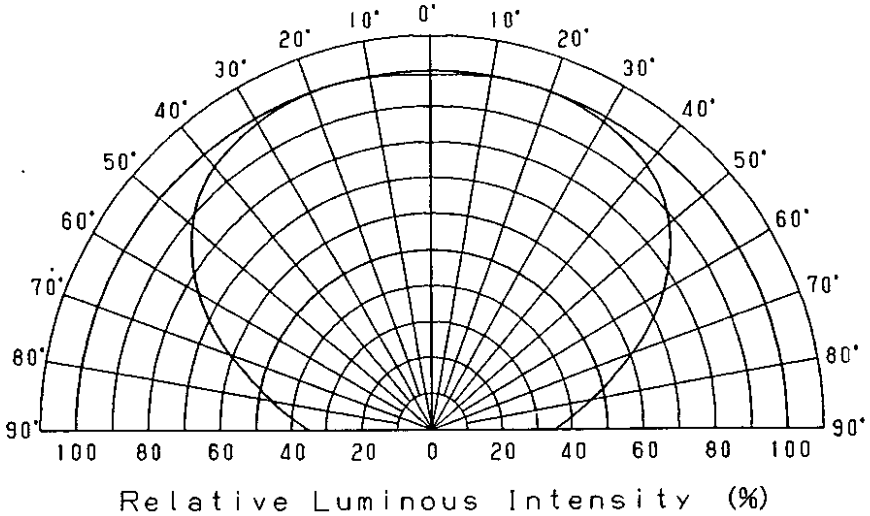
Relative Luminous Intensity
Wavelength Characteristics

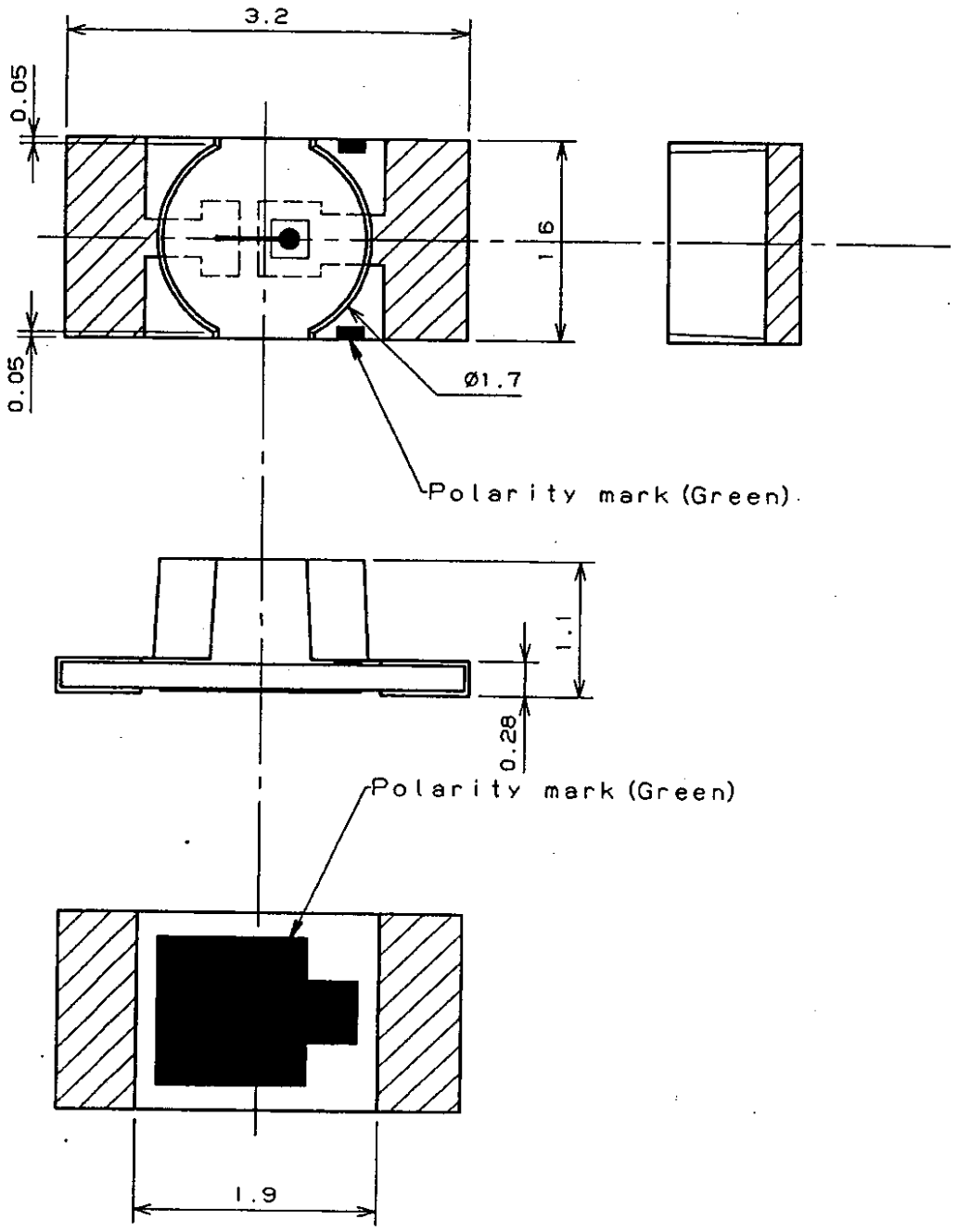


Directive Characteristics



Oct.20.2001			

Approved	Checked	Designed	DEVELOPMENT SPECIFICATION (OUTLINE)	
K.Yama.	T.Ikeda	T.Tabata	P/N:	



ANODE — CATHODE

(NOTE)
1. Unit: mm
2. Tolerance unless specified is ±0.15.
3. ▨ indicate Au terminal.

Jan.14.1999			